

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max $T_A = +25^\circ\text{C}$
60V	$2\Omega @ V_{GS} = 10V$	250mA
	$3\Omega @ V_{GS} = 5V$	

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

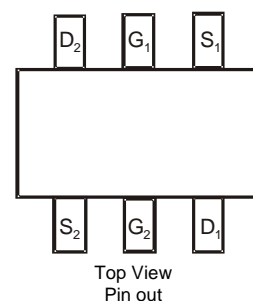
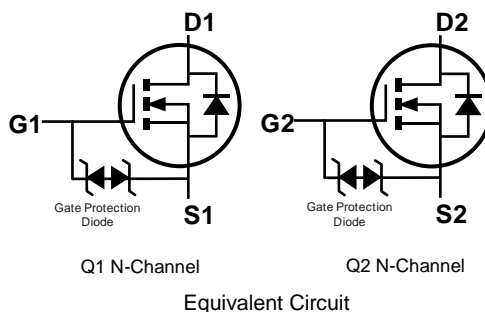
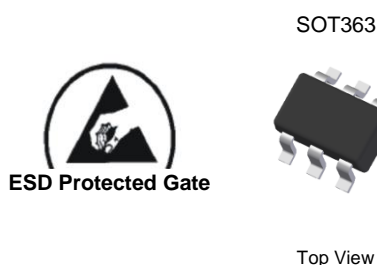
- Motor Control
- Power Management Functions

Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 ③
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)

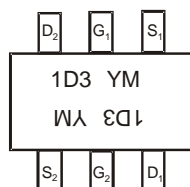


Ordering Information (Note 4)

Part Number	Case	Packaging
DMN63D1LDW-7	SOT363	3000/Tape & Reel
DMN63D1LDW-13	SOT363	10000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds..
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



1D3 = Product Type Marking Code
 YM = Date Code Marking
 Y or Y = Year (ex: B = 2014)
 M = Month (ex: 9 = September)

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	B	C	D	E	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	250 200	mA
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	0.5	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%) (Note 6)			I _{DM}	1.2	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			P _D	310	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		R _{θJA}	414	°C/W
Total Power Dissipation (Note 6)			P _D	390	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		R _{θJA}	324	°C/W
Operating and Storage Temperature Range			T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 10μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	1.6	2.5	V	V _{DS} = 10V, I _D = 1mA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	—	2.0	Ω	V _{GS} = 10V, I _D = 0.5A
		—	—	3.0		V _{GS} = 5V, I _D = 0.05A
Forward Transfer Admittance	Y _{fs}	80	—	—	mS	V _{DS} = 10V, I _D = 0.2A
Diode Forward Voltage	V _{SD}	—	0.75	1.1	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	30	—	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	4.2	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	2.9	—	pF	
Gate Resistance	R _g	—	133	—	Ω	f = 1MHz, V _{GS} = 0V, V _{DS} = 0V
Total Gate Charge	Q _g	—	304	—	pC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 250mA
Gate-Source Charge	Q _{gs}	—	203	—	pC	
Gate-Drain Charge	Q _{gd}	—	84	—	pC	
Turn-On Delay Time	t _{D(ON)}	—	3.9	—	ns	V _{DD} = 30V, V _{GS} = 10V, R _G = 25Ω, I _D = 200mA
Turn-On Rise Time	t _R	—	3.4	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	15.7	—	ns	
Turn-Off Fall Time	t _F	—	9.9	—	ns	

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 - Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

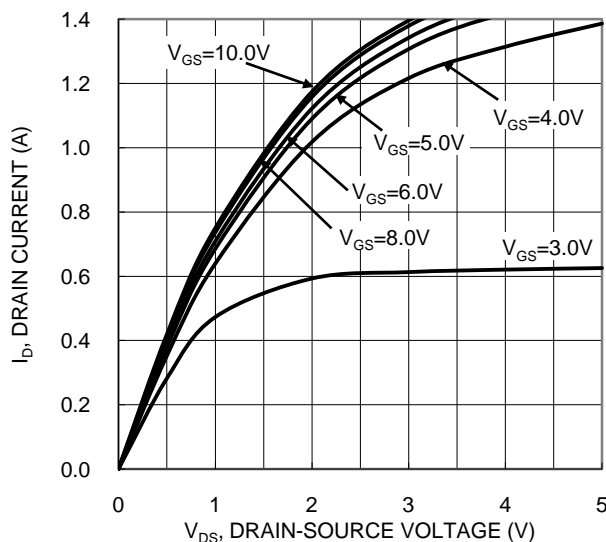


Figure 1. Typical Output Characteristic

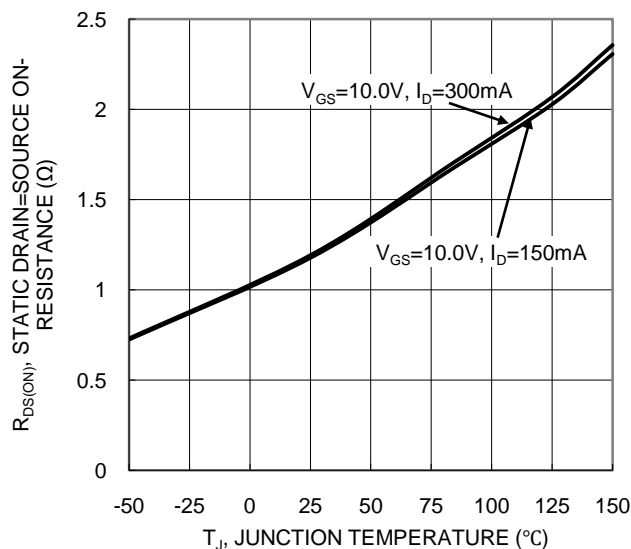


Figure 2. On-Resistance Variation with Temperature

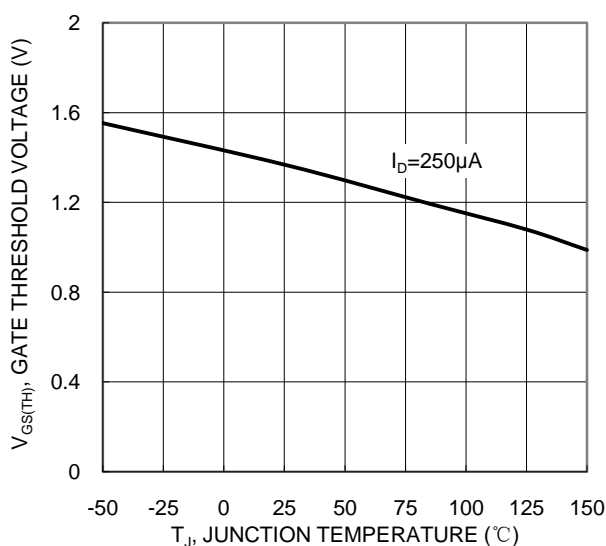


Figure 3. Gate Threshold Variation with Temperature

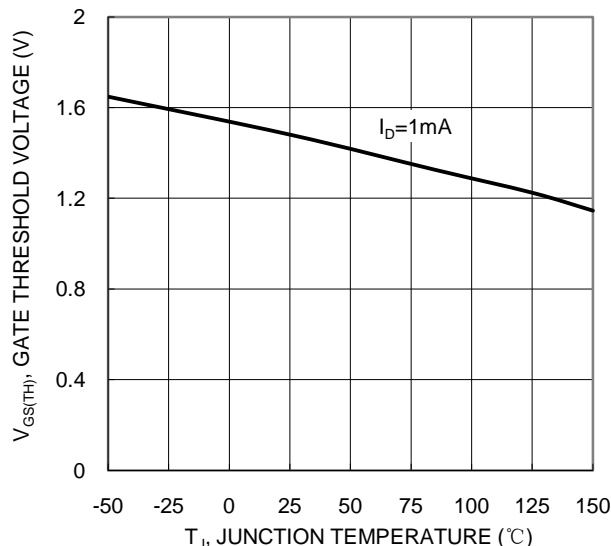


Figure 4. Gate Threshold Variation with Temperature

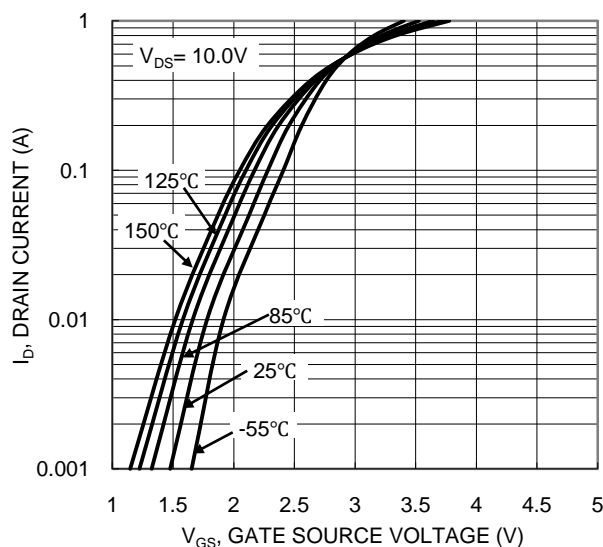


Figure 5. Typical Transfer Characteristics

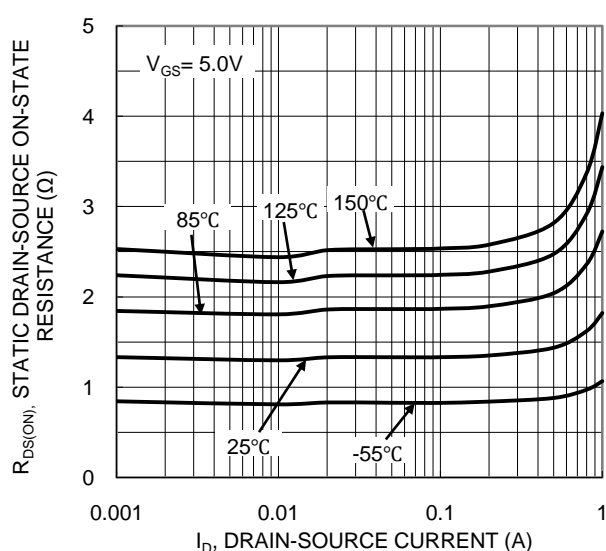


Figure 6. Static Drain-Source On-Resistance vs. Drain Current

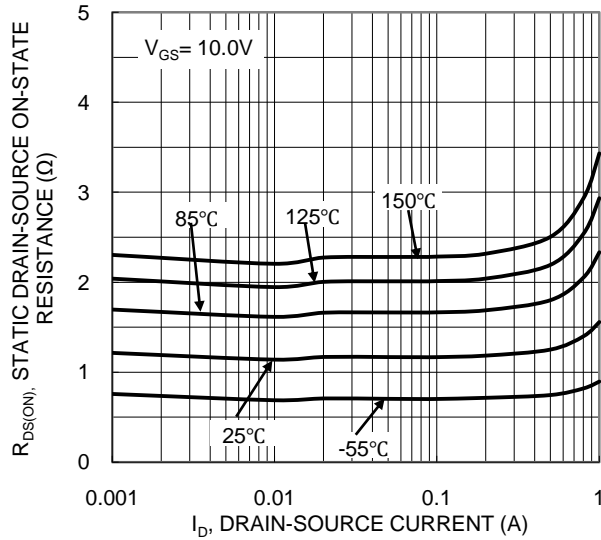


Figure 7. Static Drain-Source On-Resistance vs. Drain Current

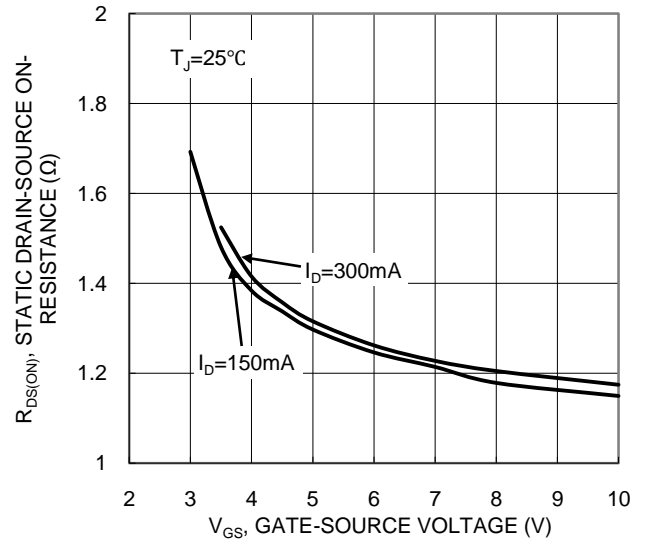


Figure 8. Static Drain-Source On-Resistance vs. Gate-Source Voltage

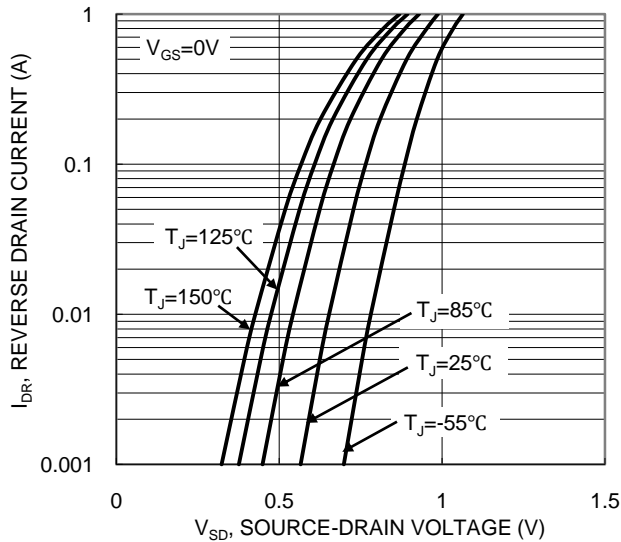


Figure 9. Reverse Drain Current

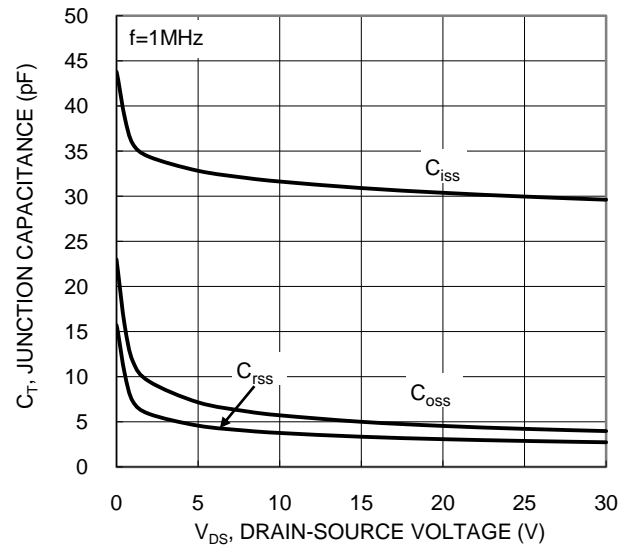


Figure 10. Typical Junction Capacitance

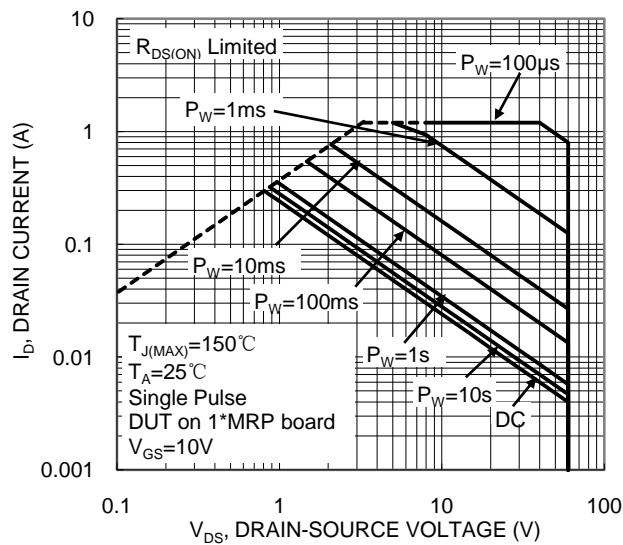
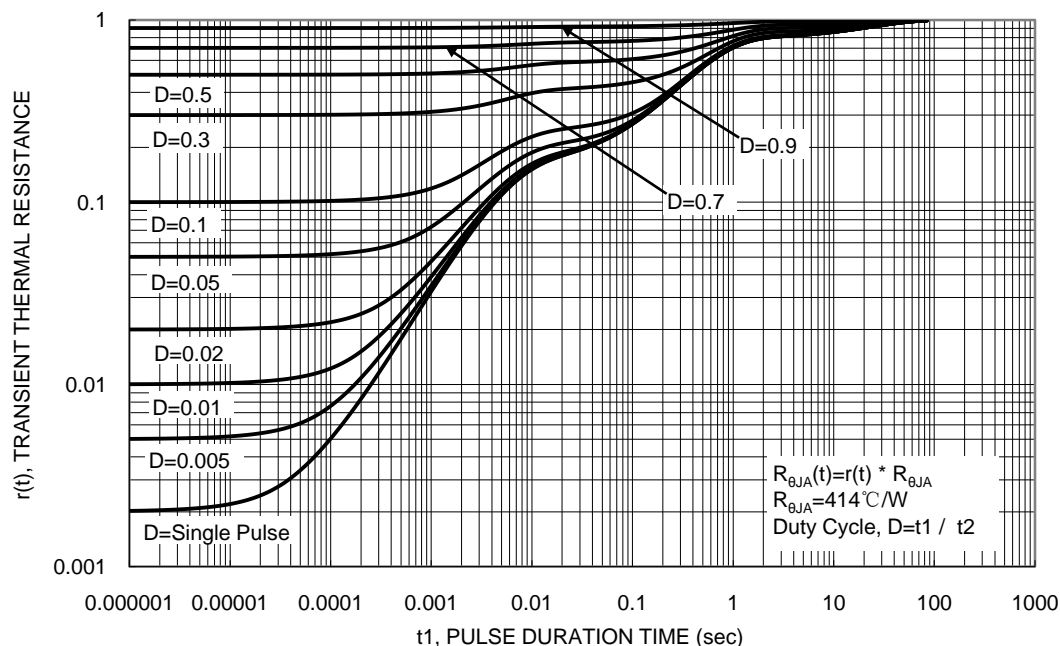
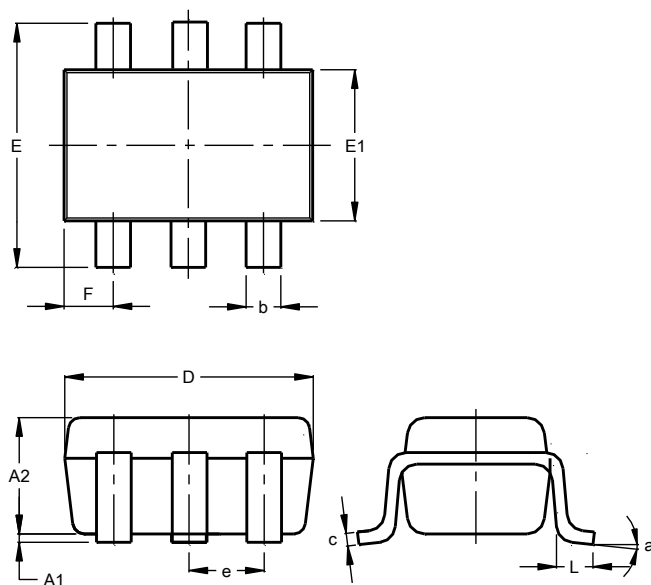


Figure 11. SOA, Safe Operation Area



Package Outline Dimensions

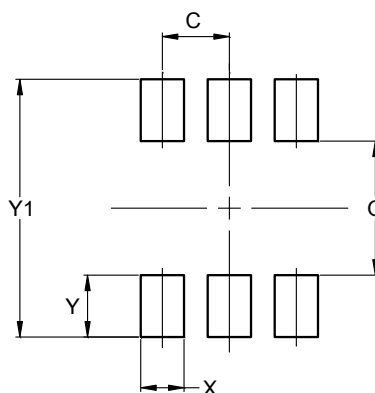
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT363			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	1.00
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	8°		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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